

isc Silicon NPN Power Transistor

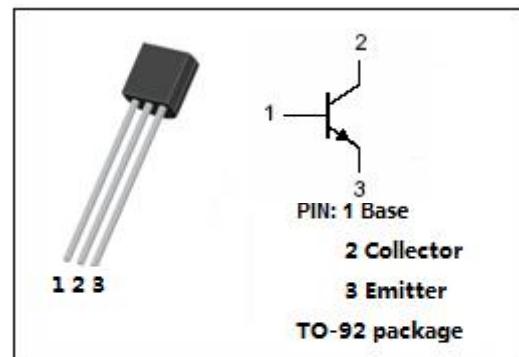
2SC2705

DESCRIPTION

- Collector-Emitter sustaining Voltage : $V_{CEO}=150V$ (Min)
- Good Linearity of h_{FE}
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

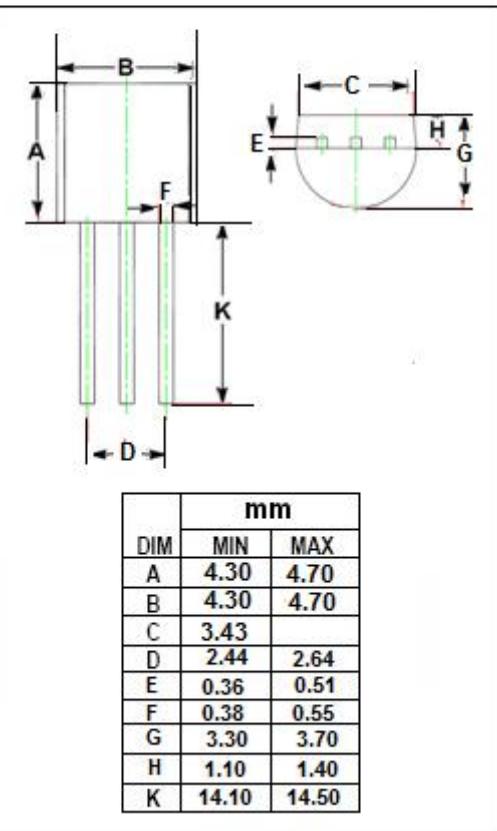
APPLICATIONS

- Audio Frequency Amplifier Applications



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	5	V
I_c	Collector Current-Continuous	50	mA
I_B	Base Current- Continuous	5	mA
P_c	Total Power Dissipation @ $T_c=25^\circ C$	800	mW
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature Range	-55~150	°C



isc Silicon NPN Power Transistor**2SC2705****ELECTRICAL CHARACTERISTICS** $T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(BR)}$	Collector-Emitter Breakdown Voltage	$I_C=30\text{mA} ; I_B= 0$	150			V
$V_{CE(\text{sat})}$	Collector-Emitter Saturation Voltage	$I_C= 10\text{mA} ; I_B= 1\text{mA}$			1.0	V
$V_{BE(\text{sat})}$	Base-Emitter Voltage	$I_C= 10\text{mA} ; V_{CE}=5\text{V}$			0.8	V
I_{CEO}	Collector Cutoff Current	$V_{CE}= 150\text{V} ; I_E= 0$			0.1	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V} ; I_C= 0$			0.1	μA
h_{FE}	DC Current Gain	$I_C=10\text{mA} ; V_{CE}=5\text{V}$	80		240	